Narcs Mestres

List of Publications by Year in Descending Order

206 papers	3,560 citations	30 h-index	52 g-index
217 ext. papers	3,805 ext. citations	4.1 avg, IF	4.41 L-index

#	Paper	IF	Citations
206	Potential of Copper Oxide High-Temperature Superconductors for Tailoring Ferromagnetic Spin Textures **2021**, 167-182		
205	Low-Fluorine Ba-Deficient Solutions for High-Performance Superconducting YBCO Films. *Coatings*, **2021**, 11, 199	2.9	2
204	Luminescent and Magnetic Tb-MOF Flakes Deposited on Silicon. *Molecules*, **2021**, 26,	4.8	2
203	Crystal engineering and ferroelectricity at the nanoscale in epitaxial 1D manganese oxide on silicon. *Nanoscale*, **2021**, 13, 9615-9625	7.7	1
202	Aqueous Chemical Solution Deposition of Functional Double Perovskite Epitaxial Thin Films. *Chemistry - A European Journal*, **2020**, 26, 9338-9347	4.8	7
201	Spectroscopic study of partially oxidized BN nanoscrolls induced by low frequency ultrasonic irradiation. *Applied Surface Science*, **2020**, 515, 146055	6.7	1
200	Rapid Thermal Annealing of Double Perovskite Thin Films Formed by Polymer Assisted Deposition. *Materials*, **2020**, 13,	3.5	1
199	Direct Visualization of Current-Stimulated Oxygen Migration in YBaCuO Thin Films. *ACS Nano*, **2020**, 14, 11765-11774	16.7	7
198	Spontaneous in-flight assembly of magnetic nanoparticles into macroscopic chains. *Nanoscale*, **2019**, 11, 14194-14202	7.7	16
197	Spontaneous cationic ordering in chemical-solution-grown La2CoMnO6 double perovskite thin films. *NPG Asia Materials*, **2019**, 11,	10.3	10
196	Dynamic magnetic properties and spin pumping in polymer-assisted-deposited La0.92MnO3 thin films. *Journal of Materials Chemistry C*, **2019**, 7, 12633-12640	7.1	3
195	Electromigration in the dissipative state of high-temperature superconducting bridges. *Applied Physics Letters*, **2019**, 114, 012601	3.4	4
194	Electrochemical Tuning of Metal Insulator Transition and Nonvolatile Resistive Switching in Superconducting Films. *ACS Applied Materials & Interfaces*, **2018**, 10, 30522-30531	9.5	12
193	2D organic molecular metallic soft material derived from BEDO-TTF with electrochromic and rectifying properties. *Npj Flexible Electronics*, **2018**, 2,	10.7	1
192	E-MRS spring meeting 2016 symposium AA: solution processing and properties of functional oxide thin films and nanostructures II. *Journal of Sol-Gel Science and Technology*, **2017**, 81, 311-312	2.3	
191	Petrographic and geochemical evidence for multiphase formation of carbonates in the Martian orthopyroxenite Allan Hills 84001. *Meteoritics and Planetary Science*, **2017**, 52, 1030-1047	2.8	6
190	Chelyabinsk Meteorite as a Proxy for Studying the Properties of Potentially Hazardous Asteroids and Impact Deflection Strategies. *Thirty Years of Astronomical Discovery With UKIRT*, **2017**, 219-241	0.3	3

189	Development of Epitaxial Oxide Ceramics Nanomaterials Based on Chemical Strategies on Semiconductor Platforms **2016**, 1-32		
188	Formation of Self-Organized Mn3O4 Nanoinclusions in LaMnO3 Films. *Frontiers in Physics*, **2016**, 4,	3.9	5
187	One-Step Route to Iron Oxide Hollow Nanocuboids by Cluster Condensation: Implementation in Water Remediation Technology. *ACS Applied Materials & Interfaces*, **2016**, 8, 28599-28606	9.5	16
186	Multiwavelength excitation Raman scattering analysis of bulk and two-dimensional MoS 2 : vibrational properties of atomically thin MoS 2 layers. *2D Materials*, **2015**, 2, 035006	5.9	73
185	Tuning the Terrace and Step Stability of 6H-SiC (0001) for Graphene Film Deposition. *Materials Science Forum*, **2015**, 821-823, 953-956	0.4	
184	Chemical solution growth of La0.7Sr0.3MnO3 nanotubes in confined geometries. *Journal of Sol-Gel Science and Technology*, **2015**, 73, 620-627	2.3	1
183	Integration of functional complex oxide nanomaterials on silicon. *Frontiers in Physics*, **2015**, 3,	3.9	4
182	Ferromagnetic 1D oxide nanostructures grown from chemical solutions in confined geometries. *Chemical Society Reviews*, **2014**, 43, 2042-54	58.5	14
181	Fabrication of highly regular suspended graphene nanoribbons through a one-step electron beam lithography process. *Microelectronic Engineering*, **2014**, 129, 81-85	2.5	11
180	Direct Monolithic Integration of Vertical Single Crystalline Octahedral Molecular Sieve Nanowires on Silicon. *Chemistry of Materials*, **2014**, 26, 1019-1028	9.6	11
179	Thickness□oncentration□iscosity relationships in spin-coated metalorganic ceria films containing polyvinylpyrrolidone. *Journal of Sol-Gel Science and Technology*, **2014**, 72, 21-29	2.3	6
178	Chemical solution route to self-assembled epitaxial oxide nanostructures. *Chemical Society Reviews*, **2014**, 43, 2200-25	58.5	78
177	Electronic and magnetic structure of LaSr-2□ manganese oxide molecular sieve nanowires. *Microscopy and Microanalysis*, **2014**, 20, 760-6	0.5	6
176	The Ard□ L6 ordinary chondrite: A long-hidden Spanish meteorite fall. *Meteoritics and Planetary Science*, **2014**, 49, 1475-1484	2.8	3
175	Magnetic vortex evolution in self-assembled La0.7Sr0.3MnO3 nanoislands under in-plane magnetic field. *APL Materials*, **2014**, 2, 076111	5.7	5
174	Enabling electromechanical transduction in silicon nanowire mechanical resonators fabricated by focused ion beam implantation. *Nanotechnology*, **2014**, 25, 135302	3.4	23
173	Formation of Graphene onto Atomically Flat 6H-SiC. *Materials Science Forum*, **2014**, 778-780, 1158-1161	0.4	1
172	Focused ion beam as a tool for graphene technology: Structural study of processing sequence by electron microscopy. *Japanese Journal of Applied Physics*, **2014**, 53, 02BC22	1.4	1

171	Nanosession: Valence Change Memories - A Look Inside **2013**, 233-245		
170	Functional oxide nanostructures written by EBL on insulating single crystal substrates. *Microelectronic Engineering*, **2013**, 110, 94-99	2.5	3
169	Photoemission electron microscopy study of sub-200 nm self-assembled La□Sr□MnO□ epitaxial islands. *Nanoscale*, **2013**, 5, 2990-8	7.7	9
168	Thermal Analysis for Low Temperature Synthesis of Oxide Thin Films from Chemical Solutions. *Journal of Physical Chemistry C*, **2013**, 117, 20133-20138	3.8	37
167	Metal-Induced Crystallization of Focused Ion Beam-Induced Deposition for Functional Patterned Ultrathin Nanocarbon. *Lecture Notes in Nanoscale Science and Technology*, **2013**, 123-159	0.3	0
166	Dual Function Polyvinyl Alcohol Based Oxide Precursors for Nanoimprinting and Electron Beam Lithography. *Materials Research Society Symposia Proceedings*, **2013**, 1547, 75-80		
165	Chemical synthesis of oriented ferromagnetic LaSr-2 □4 manganese oxide molecular sieve nanowires. *Chemical Communications*, **2012**, 48, 6223-5	5.8	9
164	Nucleation and mesostrain influence on percolating critical currents of solution derived YBa2Cu3O7 superconducting thin films. *Physica C: Superconductivity and Its Applications*, **2012**, 482, 58-67	1.3	37
163	Nanoscale magnetic structure and properties of solution-derived self-assembled La0.7Sr0.3MnO3 islands. *Journal of Applied Physics*, **2012**, 111, 024307	2.5	27
162	Interface structure governed by plastic and structural dissimilarity in perovskite La0.7Sr0.3MnO3 nanodots on rock-salt MgO substrates. *Applied Physics Letters*, **2012**, 100, 083104	3.4	3
161	Synthesis of patterned nanographene on insulators from focused ion beam induced deposition of carbon. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 03D113	1.3	5
160	Single crystalline La0.7Sr0.3MnO3 molecular sieve nanowires with high temperature ferromagnetism. *Journal of the American Chemical Society*, **2011**, 133, 4053-61	16.4	20
159	High temperature transformation of electrospun BaZrO3 nanotubes into nanoparticle chains. *CrystEngComm*, **2011**, 13, 7224	3.3	10
158	Characterisation of HfO2/Si/SiC MOS Capacitors. *Materials Science Forum*, **2011**, 679-680, 674-677	0.4	
157	Nanobaguettes Single Epitaxial Graphene Layers on SiC(11-20). *Materials Science Forum*, **2011**, 679-680, 781-784	0.4	2
156	Deposited Thin SiO[sub 2] for Gate Oxide on n-Type and p-Type GaN. *Journal of the Electrochemical Society*, **2010**, 157, H1008	3.9	15
155	SiC on SOI Resonators: A Route for Electrically Driven MEMS in Harsh Environment. *Materials Science Forum*, **2010**, 645-648, 845-848	0.4	1
154	Differences between Graphene Grown on Si-Face and C-Face. *Materials Science Forum*, **2010**, 645-648, 581-584	0.4	2

153	Growth of monolayer graphene on 8° off-axis 4H-SiC (0001) substrates with application to quantum transport devices. *Applied Physics Letters*, **2010**, 97, 093107	3.4	20
152	Integration of HfO2 on Si/SiC heterojunctions for the gate architecture of SiC power devices. *Applied Physics Letters*, **2010**, 97, 013506	3.4	8
151	Analysis of Excess Carrier Concentration Control in Fast-Recovery High Power Bipolar Diodes at Low Current Densities. *Journal of the Electrochemical Society*, **2010**, 157, H711	3.9	7
150	Current status of self-organized epitaxial graphene ribbons on the C face of 6H-SiC substrates. *Journal Physics D: Applied Physics*, **2010**, 43, 374011	3	27
149	3C-SiC films on insulated substrates for high-temperature electrostatic-based resonators. *Journal of Micromechanics and Microengineering*, **2010**, 20, 115007	2	4
148	Orientational ordering of solution derived epitaxial Gd-doped ceria nanowires induced by nanoscratching. *Nanotechnology*, **2010**, 21, 025302	3.4	13
147	Location of hot spots in integrated circuits by monitoring the substrate thermal-phase lag with the mirage effect. *Optics Letters*, **2010**, 35, 2657-9	3	6
146	Vertical (La,Sr)MnO3 Nanorods from Track-Etched Polymers Directly Buffering Substrates. *Advanced Functional Materials*, **2010**, 20, 892-897	15.6	16
145	Vertical Nanostructures: Vertical (La,Sr)MnO3 Nanorods from Track-Etched Polymers Directly Buffering Substrates (Adv. Funct. Mater. 6/2010). *Advanced Functional Materials*, **2010**, 20, n/a-n/a	15.6	1
144	Interfacial properties of AlN and oxidized AlN on Si. *Surface Science*, **2010**, 604, 63-67	1.8	9
143	Nanostructuring of epitaxial graphene layers on SiC by means of field-induced atomic force microscopy modification. *Journal of Vacuum Science & Technology B*, **2009**, 27, 3149		15
142	Fabrication of complementary metal-oxide-semiconductor integrated nanomechanical devices by ion beam patterning. *Journal of Vacuum Science & Technology B*, **2009**, 27, 2691		13
141	Growth of Few Graphene Layers on 6H, 4H and 3C-SiC Substrates. *Materials Science Forum*, **2009**, 615-617, 203-206	0.4	2
140	Rich Phase Behavior in a Supramolecular Conducting Material Derived from an Organogelator. *Advanced Functional Materials*, **2009**, 19, 934-941	15.6	30
139	Effects of cap layer on ohmic Ti/Al contacts to Si+ implanted GaN. *Applied Surface Science*, **2009**, 255, 6057-6060	6.7	25
138	Highly sensitive strained AlN on Si(111) resonators. *Sensors and Actuators A: Physical*, **2009**, 150, 64-68	3.9	10
137	Anisotropic growth of long isolated graphene ribbons on the C face of graphite-capped 6H-SiC. *Physical Review B*, **2009**, 80,	3.3	81
136	Ohmic Contacts to implanted GaN **2009**,		1

135	Laser beam deflection-based perimeter scanning of integrated circuits for local overheating location. *Journal Physics D: Applied Physics*, **2009**, 42, 012002	3	4
134	Selective epitaxial growth of graphene on SiC. *Applied Physics Letters*, **2008**, 93, 123503	3.4	37
133	Hot-Spot Detection in Integrated Circuits by Substrate Heat-Flux Sensing. *IEEE Electron Device Letters*, **2008**, 29, 1142-1144	4.4	14
132	Steady-state sinusoidal thermal characterization at chip level by internal infrared-laser deflection. *Journal Physics D: Applied Physics*, **2008**, 41, 155508	3	14
131	Early stage formation of graphene on the C face of 6H-SiC. *Applied Physics Letters*, **2008**, 93, 263102	3.4	37
130	Single-Crystalline La0.7Sr0.3MnO3 Nanowires by Polymer-Template-Directed Chemical Solution Synthesis. *Advanced Materials*, **2008**, 20, 3672-3677	24	36
129	CVD oriented growth of carbon nanotubes using AlPO4-5 and L type zeolites. *Microelectronic Engineering*, **2008**, 85, 1202-1205	2.5	8
128	Fabrication of monocrystalline 3C-SiC resonators for MHz frequency sensors applications. *Sensors and Actuators B: Chemical*, **2008**, 133, 276-280	8.5	22
127	SiC MOSFETs with thermally oxidized Ta2Si stacked on SiO2 as high-k gate insulator. *Microelectronic Engineering*, **2008**, 85, 704-709	2.5	8
126	Local growth of carbon nanotubes by thermal chemical vapor deposition from iron based precursor nanoparticles **2007**,		2
125	Strong isotropic flux pinning in solution-derived YBa2Cu3O7-x nanocomposite superconductor films. *Nature Materials*, **2007**, 6, 367-73	27	509
124	SiC MOSFET Channel Mobility Dependence on Substrate Doping and Temperature Considering High Density of Interface Traps. *Materials Science Forum*, **2007**, 556-557, 835-838	0.4	5
123	Fabrication and Test of 3C-SiC Electrostatic Resonators. *Materials Science Forum*, **2007**, 556-557, 949-952	0.4	
122	Depth-Resolved Temperature Measurements on Power Devices under Transient Conditions **2007**,		1
121	Analysis of 1.2 kV JBS rectifiers fabricated in 4H-SiC. *Semiconductor Science and Technology*, **2006**, 21, 670-676	1.8	12
120	Transmission Fabry-Pérot interference thermometry for thermal characterization of microelectronic devices. *Semiconductor Science and Technology*, **2006**, 21, 1537-1542	1.8	12
119	Modelling of the Anomalous Field-Effect Mobility Peak of O-Ta2Si/4H-SiC High-k MOSFETs Measured in Strong Inversion. *Materials Science Forum*, **2006**, 527-529, 1059-1062	0.4	
118	Impact of Annealing Temperature Ramps on the Electrical Activation of N+ and P+ Co-Implanted SiC Layers. *Materials Science Forum*, **2006**, 527-529, 795-798	0.4	2

117	Interface control in all metalorganic deposited coated conductors: Influence on critical currents. *Journal of Materials Research*, **2006**, 21, 2176-2184	2.5	12
116	PECVD Deposited TEOS for Field-Effect Mobility Improvement in 4H-SiC MOSFETs on the (0001) and (11-20) Faces. *Materials Science Forum*, **2006**, 527-529, 1047-1050	0.4	3
115	All-chemical high-Jc YBa2Cu3O7 multilayers with SrTiO3 as cap layer. *Journal of Materials Research*, **2006**, 21, 1106-1116	2.5	18
114	Field-effect mobility temperature modeling of 4H-SiC metal-oxide-semiconductor transistors. *Journal of Applied Physics*, **2006**, 100, 114508	2.5	77
113	Progress towards all-chemical superconducting YBa2Cu3O7-coated conductors. *Superconductor Science and Technology*, **2006**, 19, S13-S26	3.1	199
112	Smooth Stress Relief of Trifluoroacetate Metal-Organic Solutions for YBa2Cu3O7Film Growth. *Chemistry of Materials*, **2006**, 18, 5897-5906	9.6	64
111	Precursor Evolution and Nucleation Mechanism of YBa2Cu3Ox Films by TFA Metal□Organic Decomposition. *Chemistry of Materials*, **2006**, 18, 6211-6219	9.6	55
110	Nucleation Mechanism OF YBa2Cu3O7by CSD using TFA Precursors. *Journal of Physics: Conference Series*, **2006**, 43, 321-324	0.3	1
109	Electrosynthesis of the poly(N-vinyl carbazole)/carbon nanotubes composite for applications in the supercapacitors field. *European Polymer Journal*, **2006**, 42, 2302-2312	5.2	38
108	A field-effect electron mobility model for SiC MOSFETs including high density of traps at the interface. *Microelectronic Engineering*, **2006**, 83, 440-445	2.5	41
107	Ta 2 Si short time thermal oxidized layers in N 2 O and O 2 to form high- k gate dielectric on SiC. *Applied Surface Science*, **2006**, 253, 1741-1744	6.7	2
106	A study of the influence of the annealing processes and interfaces with deposited SiO2 from tetra-ethoxy-silane for reducing the thermal budget in the gate definition of 4H□SiC devices. *Thin Solid Films*, **2006**, 513, 248-252	2.2	10
105	Characterisation of YBa2Cu3O6+x films grown by the trifluoro-acetate metal organic decomposition route by infrared spectroscopy. *Thin Solid Films*, **2006**, 515, 1607-1611	2.2	4
104	High J/sub c/ YBCO thin films and multilayers grown by chemical solution deposition. *IEEE Transactions on Applied Superconductivity*, **2005**, 15, 2747-2750	1.8	2
103	Ni/Ti ohmic and Schottky contacts on 4H-SiC formed with a single thermal treatment. *Diamond and Related Materials*, **2005**, 14, 1146-1149	3.5	35
102	Composite structure of wood cells in petrified wood. *Materials Science and Engineering C*, **2005**, 25, 119-130	1.8	33
101	Planar edge termination design and technology considerations for 1.7-kV 4H-SiC PiN diodes. *IEEE Transactions on Electron Devices*, **2005**, 52, 2309-2316	2.9	59
100	Barrier inhomogeneities and electrical characteristics of Ni/Ti bilayer Schottky contacts on 4H□SiC after high temperature treatments. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 692-697	1.6	25

99	Full wafer size investigation of N+ and P+ co-implanted layers in 4H-SiC. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 698-704	1.6	1
98	4H-SiC MOS Structures Fabricated from RTCVD Si Layers Oxidized in Diluted N2O. *Materials Science Forum*, **2005**, 483-485, 673-676	0.4	1
97	Homogeneity of Nitrogen and Phosphorus Co-Implants in 4H-SiC: Full Wafer Scale Investigation. *Materials Science Forum*, **2005**, 483-485, 645-648	0.4	
96	Combined synchrotron x-ray diffraction and micro-Raman for following in situ the growth of solution-deposited YBa2Cu3O7 thin films. *Journal of Materials Research*, **2005**, 20, 3270-3273	2.5	5
95	Epitaxial SiC Formation at the SiO2/Si Interface by C+ Implantation into SiO2 and Subsequent Annealing. *Materials Science Forum*, **2005**, 483-485, 233-236	0.4	2
94	4H-SiC MOSFETs Using Thermal Oxidized Ta2Si Films as High-k Gate Dielectric. *Materials Science Forum*, **2005**, 483-485, 713-716	0.4	3
93	Characterization of High-k Ta[sub 2]Si Oxidized Films on 4H-SiC and Si Substrates as Gate Insulator. *Journal of the Electrochemical Society*, **2005**, 152, G259	3.9	24
92	Development of an analog processing circuit for IR-radiation power and noncontact position measurements. *Review of Scientific Instruments*, **2005**, 76, 025106	1.7	9
91	Thermal calibration procedure for internal infrared laser deflection apparatus. *Review of Scientific Instruments*, **2005**, 76, 094905	1.7	6
90	The influence of growth conditions on the microstructure and critical currents of TFA-MOD YBa2Cu3O7films. *Superconductor Science and Technology*, **2005**, 18, 1141-1150	3.1	95
89	Growth Mechanism and Opmization of MOD CeO2 Buffer Layers for TFA YBa2Cu3O7/CeO2 Multilayers. *Materials Research Society Symposia Proceedings*, **2005**, 868, 681		
88	Temperature Dependence of 4H-SiC JBS and Schottky Diodes after High Temperature Treatment of Contact Metal. *Materials Science Forum*, **2005**, 483-485, 945-948	0.4	3
87	Interface Control in All MOD Coated Conductors: Influence on Critical Currents. *Materials Research Society Symposia Proceedings*, **2005**, 868, 661		
86	Biaxial texture analysis of YBa2Cu3O7-coated conductors by micro-Raman spectroscopy. *Physical Review B*, **2004**, 70,	3.3	23
85	Flash Lamp Supported Deposition of 3C-SiC (FLASiC) – a Promising Technique to Produce High Quality Cubic SiC Layers. *Materials Science Forum*, **2004**, 457-460, 175-180	0.4	14
84	4H-SiC MIS structures using oxidized Ta2Si as high-k dielectric. *Materials Research Society Symposia Proceedings*, **2004**, 815, 88		2
83	SiC Base Micro-Probe for Myocardial Ischemia Monitoring. *Materials Science Forum*, **2004**, 457-460, 1483-1486	0.4	4
82	Formation of 3C-SiC Films Embedded in SiO2 by Sacrificial Oxidation. *Materials Science Forum*, **2004**, 457-460, 1515-1518	0.4	2

81	Room Temperature Implantation and Activation Kinetics of Nitrogen and Phosphorus in 4H-SiC Crystals. *Materials Science Forum*, **2004**, 457-460, 893-896	0.4	8
80	Electrical Characterization of Deposited and Oxidized Ta2Si as Dielectric Film for SiC Metal-Insulator-Semiconductor Structures. *Materials Science Forum*, **2004**, 457-460, 845-848	0.4	5
79	Chemical solution deposition: a path towards low cost coated conductors. *Superconductor Science and Technology*, **2004**, 17, 1055-1064	3.1	117
78	Sic Power Diodes Improvement by Fine Surface Polishing. *Materials Research Society Symposia Proceedings*, **2004**, 815, 124		3
77	Visible Light Laser Irradiation: a Tool for Implantation Damage Reduction. *Materials Science Forum*, **2004**, 457-460, 941-944	0.4	5
76	A Highly Effective Edge Termination Design for SiC Planar High Power Devices. *Materials Science Forum*, **2004**, 457-460, 1253-1256	0.4	8
75	Ta[sub 2]Si Thermal Oxidation: A Simple Route to a High-k Gate Dielectric on 4H-SiC. *Electrochemical and Solid-State Letters*, **2004**, 7, F93		5
74	Chemical solution techniques for epitaxial growth of oxide buffer and YBa2Cu3O7 films. *Journal of the European Ceramic Society*, **2004**, 24, 1831-1835	6	14
73	Self-heating experimental study of 600 V PT-IGBTs under low dissipation energies. *Microelectronics Journal*, **2004**, 35, 841-847	1.8	1
72	Chemical solution growth of superconductors: a new path towards high critical current coated conductors. *Physica C: Superconductivity and Its Applications*, **2004**, 408-410, 913-914	1.3	4
71	Internal infrared laser deflection system: a tool for power device characterization. *Measurement Science and Technology*, **2004**, 15, 1011-1018	2	23
70	Theoretical and experimental investigations of single- and multilayer structures with SiGe nanoislands. *Materials Science and Engineering C*, **2003**, 23, 1027-1031	8.3	14
69	Aging of Sr2FeMoO6 and related oxides. *Materials Research Bulletin*, **2003**, 38, 1477-1486	5.1	27
68	Comparative evaluation of implantation damage produced by N and P ions in 6H-SiC. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 875-880		4
67	Optimisation of junction termination extension for the development of a 2000 V planar 4H□SiC diode. *Diamond and Related Materials*, **2003**, 12, 1231-1235	3.5	13
66	High quality YBa2Cu3O7thin films grown by trifluoroacetates metalorganic deposition. *Superconductor Science and Technology*, **2003**, 16, 45-53	3.1	54
65	Influence of porosity on the critical currents of trifluoroacetate-MOD YBa/sub 2/Cu/sub 3/O/sub 7/ films. *IEEE Transactions on Applied Superconductivity*, **2003**, 13, 2504-2507	1.8	37
64	Quantitative Evaluation of Implantation Damage and Damage Recovery after Room Temperature Ion-Implantation of N+ and P+ Ions in 6H-SiC. *Materials Science Forum*, **2003**, 433-436, 653-656	0.4	1

63	Epitaxial nucleation and growth of buffer layers and Y123 coated conductors deposited by metal-organic decomposition. *Physica C: Superconductivity and Its Applications*, **2002**, 372-376, 806-809	1.3	9
62	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2002**, 89, 62-65	3.1	16
61	Infrared Investigation of Implantation Damage in 6H-SiC. *Materials Science Forum*, **2002**, 389-393, 859-862	2.4	5
60	Highly-Doped Implanted pn Junction for SiC Zener Diode Fabrication. *Materials Science Forum*, **2002**, 389-393, 1317-1320	0.4	3
59	Optical investigation of CdSe/ZnSe quantum nanostructures. *Semiconductor Science and Technology*, **2002**, 17, 173-177	1.8	4
58	Microscopic and optical investigation of Ge nanoislands on silicon substrates. *Nanotechnology*, **2002**, 13, 81-85	3.4	40
57	Structural and Superconducting Properties of Hg0.75Re0.25Ba2□SrxCa2Cu3O8+□ Superconductors Grown by Sol□Gel and Sealed Quartz Tube Synthesis. *Journal of Solid State Chemistry*, **2001**, 161, 355-364	3.3	5
56	Comment on □irst-principles theory of the evolution of vibrational properties with long-range order in GaInP2□*Physical Review B*, **2001**, 63,	3.3	1
55	Low-doped 6H-SiC n-type epilayers grown by sublimation epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 77, 50-54	3.1	40
54	An improved technology of 6H-SiC power diodes. *Microelectronics Journal*, **2000**, 31, 955-962	1.8	2
53	Micro-Raman study of high pressure induced graphite-diamond phase-structural transformation: The role of a nitrogen containing precursor. *Journal of Applied Physics*, **2000**, 88, 4875	2.5	5
52	Confocal Raman Microprobe of Lattice Damage in N+ Implanted 6H-SiC. *Materials Science Forum*, **2000**, 338-342, 663-666	0.4	7
51	Damage Reduction in Channeled Ion Implanted 6H-SiC. *Materials Science Forum*, **2000**, 338-342, 893-896	0.4	11
50	Confocal micro-Raman characterization of lattice damage in high energy aluminum implanted 6H-SiC. *Journal of Applied Physics*, **1999**, 85, 99-104	2.5	12
49	Lateral spread of implanted ion distributions in 6H?SiC: simulation. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 61-62, 373-377	3.1	11
48	Structure investigation of BN films grown by ion-beam-assisted deposition by means of polarised IR and Raman spectroscopy. *Surface and Coatings Technology*, **1999**, 116-119, 93-99	4.4	18
47	Synthesis and characterization of c-BN films prepared by ion beam assisted deposition and triode sputtering. *Thin Solid Films*, **1999**, 355-356, 89-95	2.2	12
46	CuPt Ordering Fingerprints of Optical Phonons in Ternary III□V Compound Semiconductors. *Physica Status Solidi (B): Basic Research*, **1999**, 215, 121-126	1.3	6

45	Confocal micro-Raman scattering and Rutherford backscattering characterization of lattice damage in aluminum implanted 6H□SiC. *Diamond and Related Materials*, **1999**, 8, 357-360	3.5	5
44	Effects of re-doping on superconducting properties and formation of Hg-1223 superconductors. *Physica C: Superconductivity and Its Applications*, **1999**, 328, 257-269	1.3	17
43	Infrared and Raman analysis of plasma CVD boron nitride thin films. *Diamond and Related Materials*, **1999**, 8, 398-401	3.5	7
42	CuPt Ordering Signatures of Phonons in GaInP2. *Materials Research Society Symposia Proceedings*, **1999**, 583, 223		
41	Compositional characterization of a-SiC:H films by infra-red spectroscopy. *Diamond and Related Materials*, **1998**, 7, 365-368	3.5	3
40	Analysis of Aluminium Ion Implantation Damage into 6H-SiC Epilayers. *Materials Science Forum*, **1998**, 264-268, 733-736	0.4	5
39	Optical study of boron nitride thin films prepared by plasma-enhanced chemical vapor deposition. *Diamond and Related Materials*, **1997**, 6, 1550-1554	3.5	12
38	Phonon Raman scattering in quantum wires. *Solid-State Electronics*, **1996**, 40, 707-710	1.7	9
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